

Two Photon Absorption TCT on HVCMOS, LGADs and pin diodes,

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Edge-TPA measurements on neutron irradiated HVCMOS (CCPDv3, 7×10^{15} neq/cm²) with improved setup and fresh LGADs and pin detectors will be presented. A first attempt to profile doping and electric field from data is envisaged.

Primary author: FERNANDEZ GARCIA, Marcos (Universidad de Cantabria (ES))

Co-authors: VILA ALVAREZ, Ivan (Universidad de Cantabria (ES)); PALOMO PINTO, Francisco Rogelio (Universidad de Cantabria (ES)); MOLL, Michael (CERN); JARAMILLO, Richard (IFCA); Dr MONTERO SANTOS, Raul (Universidad del País Vasco); Dr HIDALGO VILLENA, Salvador (Instituto de Microelectronica de Barcelona (IMB-CNM-CSIC))

Presenter: FERNANDEZ GARCIA, Marcos (Universidad de Cantabria (ES))

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